PWRLITE LD103SB6, LD103SF6

High Performance N-Ch Vertical Power JFET Transistor with Schottky

Features

- Trench Power JFET with low threshold voltage Vth.
- Device fully "ON" with Vgs = 0.7V
- Optimum for "Low Side" Buck Converters
- Optimized for Secondary Rectification in isolated DC-DC
- Low Rg and low Cds for high speed switching
- No "Body Diode"; extremely low Cds
- Added Fast Recovery Schottky Diode in same package

Applications

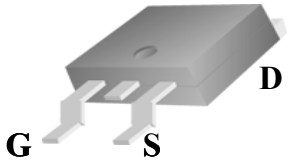
- DC-DC Converters
- Synchronous Rectifiers
- PC Motherboard Converters
- Step-down power supplies
- Brick Modules
- VRM Modules

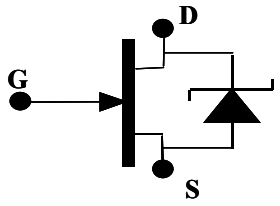
Description

The Power JFET transistor from Lovoltech is a device that presents a Low Rdson allowing for improved efficiencies in DC-DC switching applications. The device is designed with a low threshold such that drivers can operate at 5V, which reduces the driver power dissipation and increases the overall efficiency. Lower threshold produces faster turn-on/turn-off, which minimizes the required dead time. The transistor "No Body Diode" provides a very low associated parasitic capacitance Cds. A Schottky Diode is added for applications where a freewheeling diode is required. Ringing is also reduced so that a lower voltage device may be a better solution.

Preliminary

DPAK Pin Assignments





N – Channel Power JFET with Schottky Diode

Pin Definitions

Pin Number	Pin Name	Pin Function Description
1	Gate	**Gate.** Transistor Gate
2	Drain	**Drain.** Transistor Drain
3	Source	**Source.** Transistor Source

Product Summary		
V_{DS} (V)	Rdson (Ω)	I_D (A)
25V	0.0045	50

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Units
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	-10	V
Gate-Drain Voltage	V_{GD}	-28	V
Continuous Drain Current	I_D	50	A
Pulsed Drain Current	I_D	100	A
Single Pulse Drain-to-Source Avalanche Energy	E_{AS}		mJ
Junction Temperature	T_J	-55 to 150°C	°C
Storage Temperature	T_{STG}	-65 to 150°C	°C
Lead Soldering Temperature, 10 seconds	T	300°C	°C
Power Dissipation (Derated at 25°C)	P_D	80	W

Thermal Resistance

Symbol	Parameter		DPAK Ratings		Units
$R\Theta_{JA}$	Thermal Resistance Junction-to-Ambient		80		°C/W
$R\Theta_{JC}$	Thermal Resistance Junction-to-Case		1.6		°C/W

Electrical Specifications

(T_A = +25°C, unless otherwise noted.)

The ϕ denotes a specification which apply over the full operating temperature range.

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Units
	Static						
BV_{DSX}	Breakdown Voltage Drain to Source	I_G = 500 µA V_{GS}= -4 V	ϕ	25			V
BV_{GDO}	Breakdown Voltage Gate to Drain	I_G = -50µA	ϕ			-28	V
BV_{GSO}	Breakdown Voltage Gate to Source	I_G = -1 mA	ϕ		-12	-10	V
$R_{DS(ON)}$	Static Drain to Source[1] On Resistance (Current flows drain-to-source) See Fig. 1	I_G = 40 mA, I_D=10A I_G = 10 mA, I_D=10A I_G = 5 mA, I_D=10A			4.0 4.5 4.6	4.5 5.0	mΩ mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=0.1 V, I_D=250µA			-500	-400	mV
	Dynamic						
Q_G	Total Gate Charge	ΔV_{Drive}=5V, I_D=15A,V_{DS}=16V			20		nC
Q_{GD}	Gate to Drain Charge				12		nC
Q_{GS}	Gate to Source Charge				1.5		nC
Q_{SW}	Switching Charge				13.5		nC
R_G	Gate Resistance				1		Ω
$T_{D(ON)}$	Turn-on Delay Time	V_{DD}=16V, I_D=15A V_{Drive} = 5 V Clamped Inductive Load	ϕ		5		ns
T_R	Rise Time		ϕ		12		
$T_{D(OFF)}$	Turn-off Delay				2		
T_F	Fall Time				10		
C_{ISS}	Input Capacitance	V_{DS}=10V, V_{GS}= -5 V, 1MHz.			3000		pF
C_{OSS}	Output Capacitance				900		
C_{GS}	Gate-Source Capacitance				2250		
C_{GD}	Gate-Drain Capacitance				750		
C_{DS}	Drain-Source Capacitance				150		
	Schottky Diode						
B_V	Reverse Breakdown Voltage	I_R = 0.1 mA		25	30		V
I_R	Reverse Leakage	V_R=25V			0.25	0.3	mA
V_F	Forward Voltage	I_F = 1 A				400	mV
V_F	Forward Voltage	I_F = 19 A				1000	mV
V_F	Forward Voltage	I_F = 20 A			1100		mV
Qrr	Reverse Recovery Charge	I_s = 25 A di/dt = 700A/us,					nC

Notes:

1. Pulse width <= 500µs, duty cycle < = 2%

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Typical Operating Characteristics

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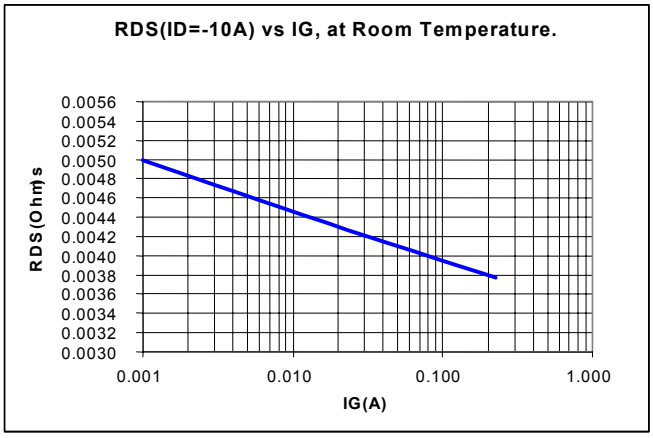

Figure 1 – R_{DSON} vs Gate Current at I_D – 10A

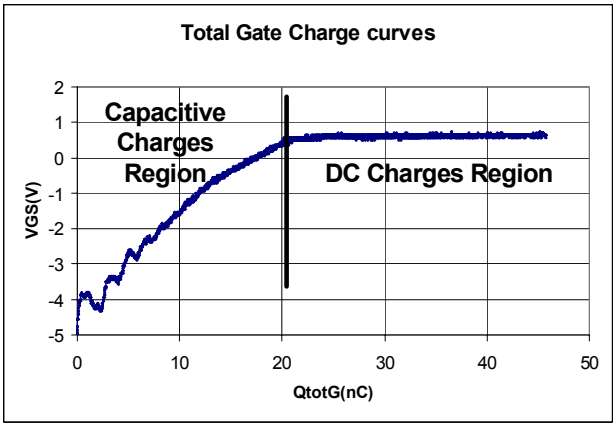

Figure 2 – Total Gate Charge

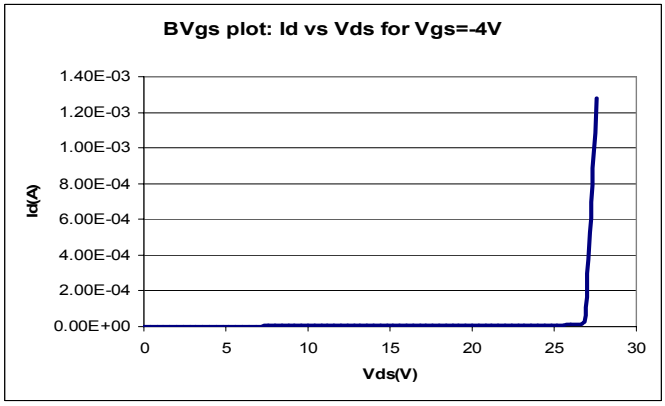

Figure 3 – Breakdown Voltage Vds vs Id

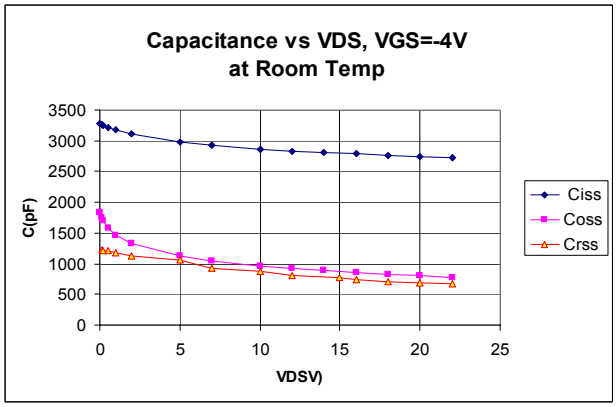

Figure 4 – Capacitance vs Drain Voltage Vds

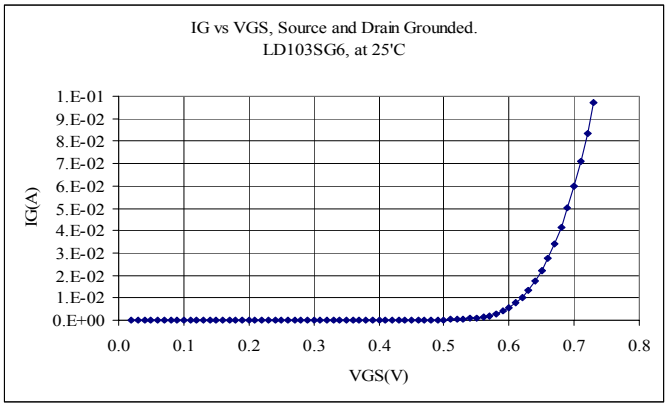

Figure 5 – I_G vs Gate Voltage V_{GS}

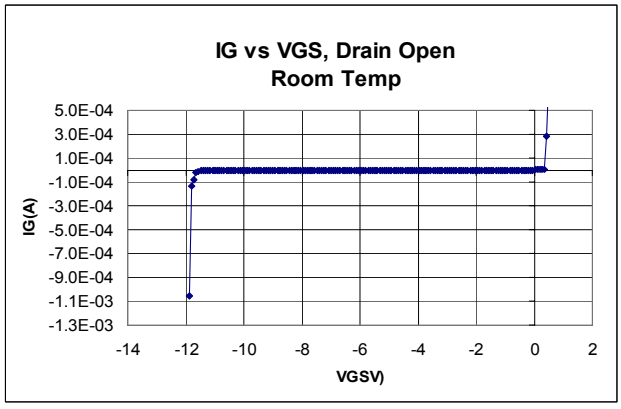

Figure 6 – Typical Gate Voltage Characteristic

Typical Operating Characteristics

(T_A = +25°C, unless otherwise noted.)

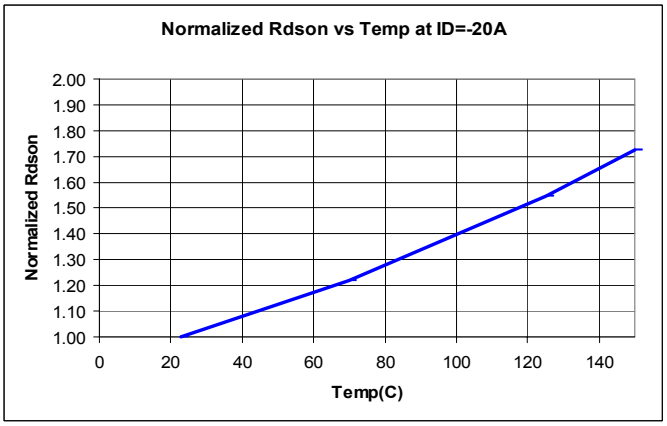

Figure 7 – R_{DSON} Temperature Coefficient

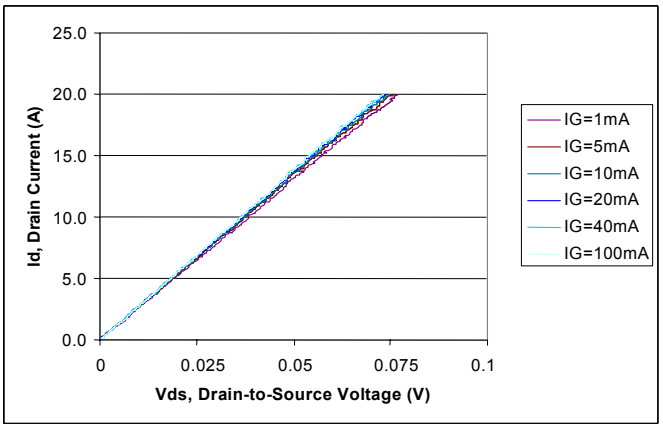

Figure 8 – On-Region Characteristics

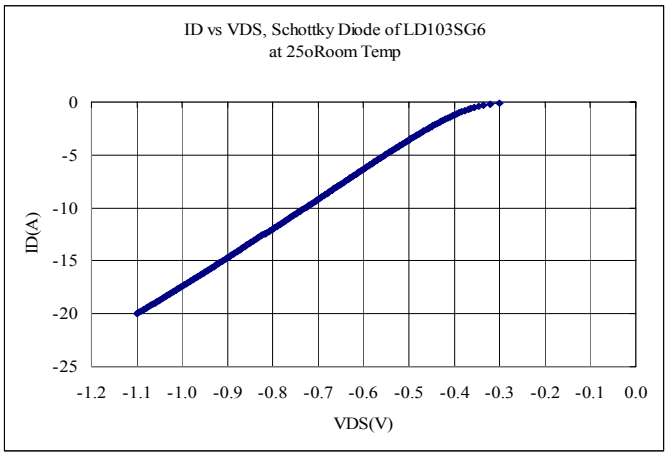

Figure 9 – Schottky Diode Voltage vs Current

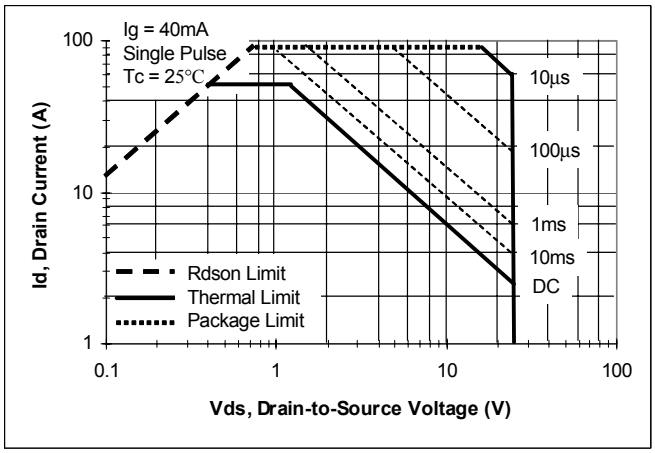

Figure 10 – Safe Operating Area

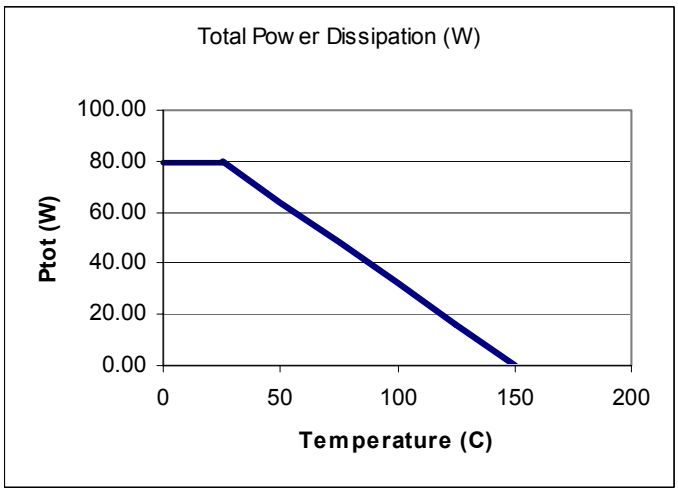

Figure 11 – Total Power Dissipation

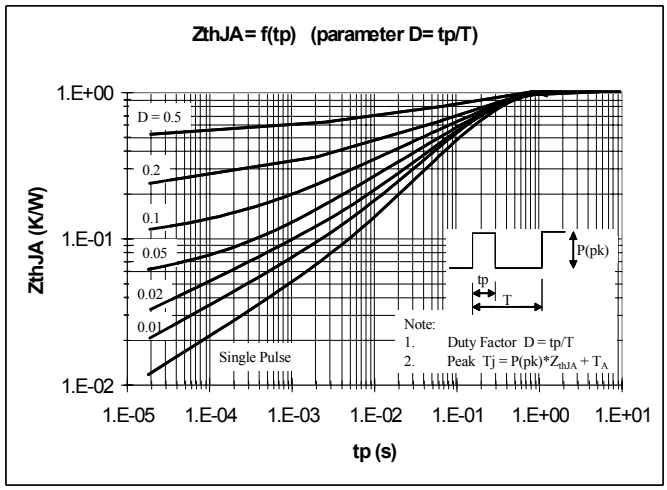

Figure 12 – Normalized Thermal Response

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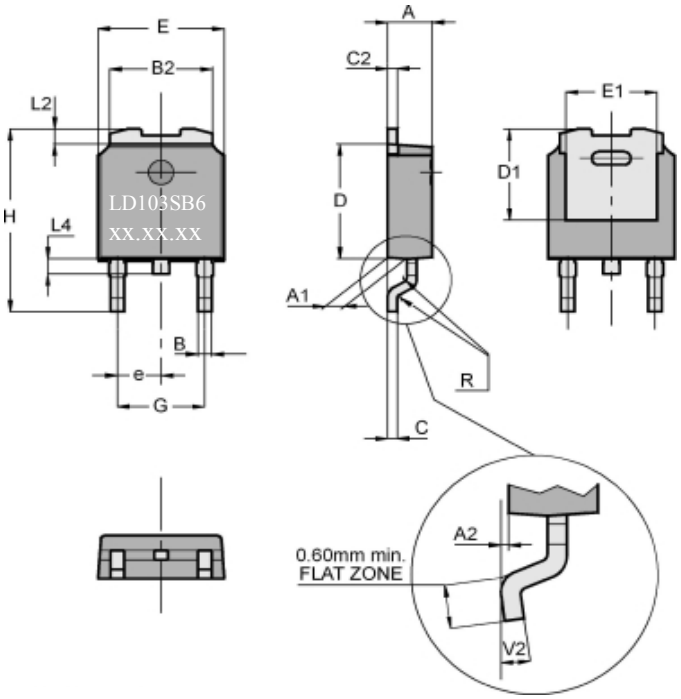
Ordering Information

Product Number	PN Marking	Package
LD103SB6	LD103SB6	TO252 (DPAK)
LD103SF6	LD103SF6	TO252 (DPAK)

Package and Marking Information

DIMENSIONS						
DIM.	mm.			inch		
	TYP.	MIN.	MAX.	TYP.	MIN.	MAX.
A		2.20	2.40		0.086	0.094
A1		0.90	1.10		0.035	0.043
A2		0.03	0.23		0.001	0.009
B		0.64	0.90		0.025	0.035
B2		5.20	5.40		0.204	0.212
C		0.45	0.60		0.017	0.023
C2		0.48	0.60		0.019	0.023
D		6.00	6.20		0.236	0.244
D1	5.10			0.201		
E		6.40	6.60		0.252	0.260
E1	4.70			0.185		
e	2.28			0.090		
G		4.40	4.60		0.173	0.181
H		9.35	10.10		0.368	0.397
L2	0.80			0.031		
L4		0.60	1.00		0.023	0.039
R	0.20			0.008		
V2		0°	8°		0°	8°



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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Datasheet Identification	Product Status	Definition
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No Identification Needed	In Production	This datasheet contains final specifications. Lovoltech reserves the right to make changes at any time without notice in order to improve the design.